

# **Phase Control Thyristor**

DS6032-1 April 2011 (LN28243)

#### **FEATURES**

- Double Side Cooling
- High Surge Capability

## **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

#### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR4440W22 DCR4440W20 DCR4440W18	2200 2000 1800	$\begin{split} &T_{vj} = \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ &I_{DRM} = I_{RRM} = 400\text{mA}, \\ &V_{DRM}, V_{RRM}  t_p = 10\text{ms}, \\ &V_{DSM}  \&  V_{RSM} = \\ &V_{DRM}  \&  V_{RRM}  + 100V \\ &\text{respectively} \end{split}$

Lower voltage grades available.

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR4440W22

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

#### **KEY PARAMETERS**

$V_{DRM}$	2200 V
$I_{T(AV)}$	4440 A
I <sub>TSM</sub>	64500 A
dV/dt*	1000 V/µs
dI/dt	250 A/μs

#### \* Higher dV/dt selections available

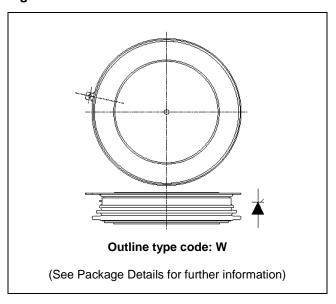


Fig. 1 Package outline



## **CURRENT RATINGS**

## $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units	
Double Si	Double Side Cooled				
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	4440	А	
I <sub>T(RMS)</sub>	RMS value	-	6970	А	
Ι <sub>Τ</sub>	Continuous (direct) on-state current	-	6280	А	

## **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current 10ms half sine, T <sub>case</sub> = 125°C		64.5	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	20.80	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.007	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Double side cooled	DC	-	0.002	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>			125	°C
T <sub>stg</sub>	Storage temperature range			-40	140	°C
F <sub>m</sub>	Clamping force			62	78	kN



## **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	400	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, ga	ate open	1000	-	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 4000A	Repetitive 50Hz	-	250	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
V <sub>T</sub>	On-state voltage	I <sub>T</sub> = 3000A, T <sub>case</sub> = 125°C			1.15	V
$V_{T(TO)}$	Threshold voltage	T <sub>case</sub> = 125°C		-	0.86	V
r <sub>T</sub>	On-state slope resistance	T <sub>case</sub> = 125°C		-	0.095	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3.0	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 5$ A/ $\mu$ s,		-	400	μs
		$dV_{DR}/dt = 20V/\mu s$ linear to 67% $V_{DRM}$				
Qs	Stored charge	$I_T = 4000A$ , $tp = 1000us, T_j = 125°C$ , $dI/dt = 5A/\mu s$ ,		- -	5000	μC
IL	Latching current	$T_j = 25$ °C,		-	1	Α
I <sub>H</sub>	Holding current	$T_j = 25$ °C,		-	200	mA

## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	rameter Test Conditions		Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	3	V
$V_{GD}$	Gate non-trigger voltage	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	300	mA
I <sub>GD</sub>	Gate non-trigger current	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	mA



#### **CURVES**

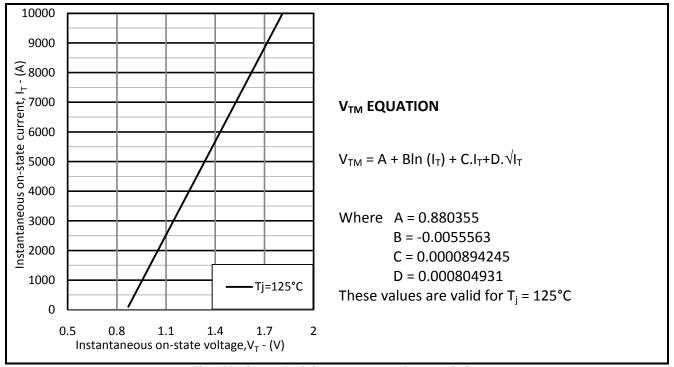


Fig.2 Maximum &minimum on-state characteristics

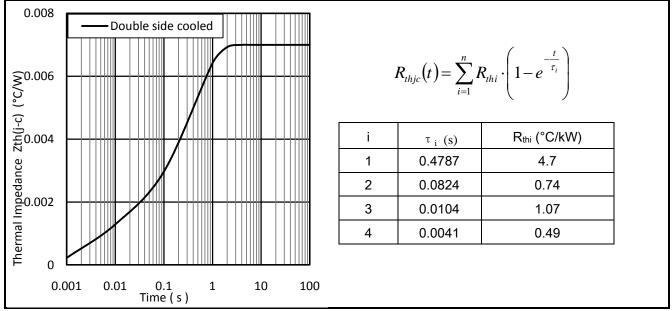
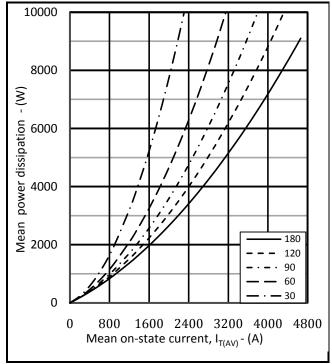


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)



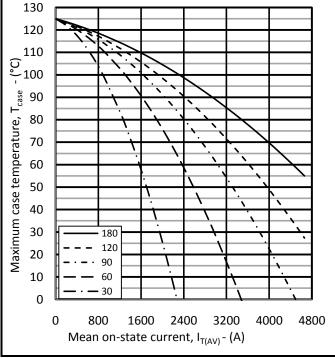


Fig.4 On-state power dissipation – sine wave

Fig.5 Maximum permissible case temperature, double side cooled – sine wave

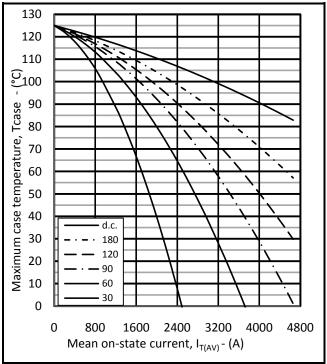


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

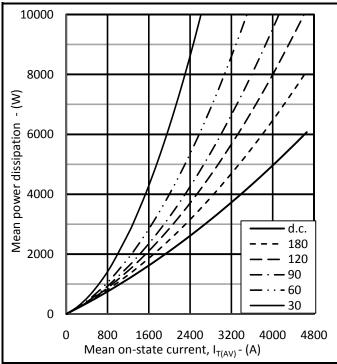
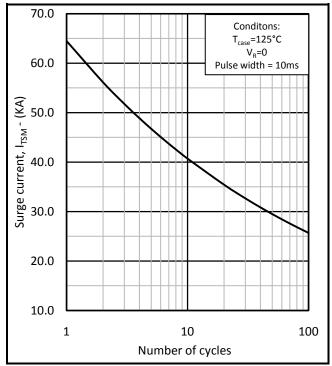


Fig.7 On-state power dissipation - rectangular wave





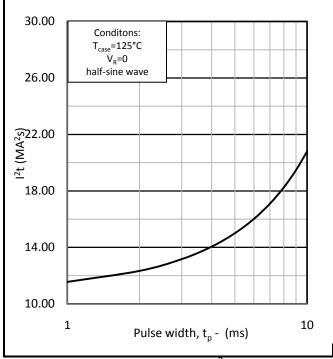


Fig.8 Multi-cycle surge current

Fig.9 Single-cycle I2t

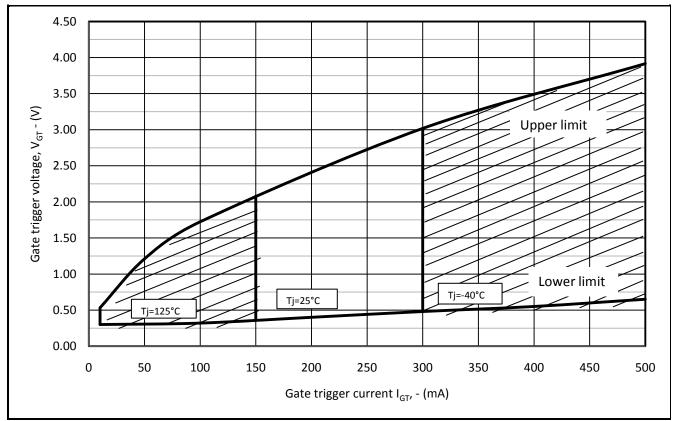


Fig.12 Gate characteristics

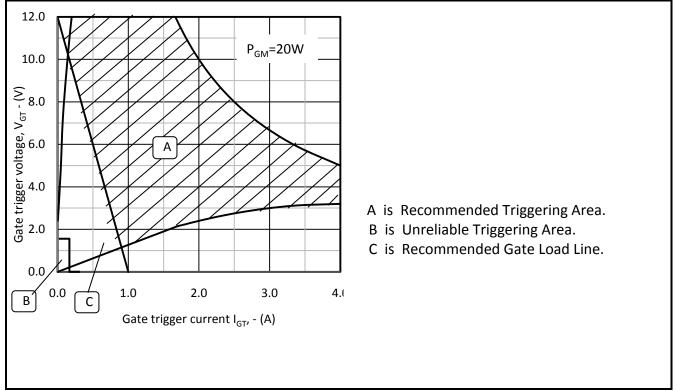


Fig.13 Gate characteristics



#### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

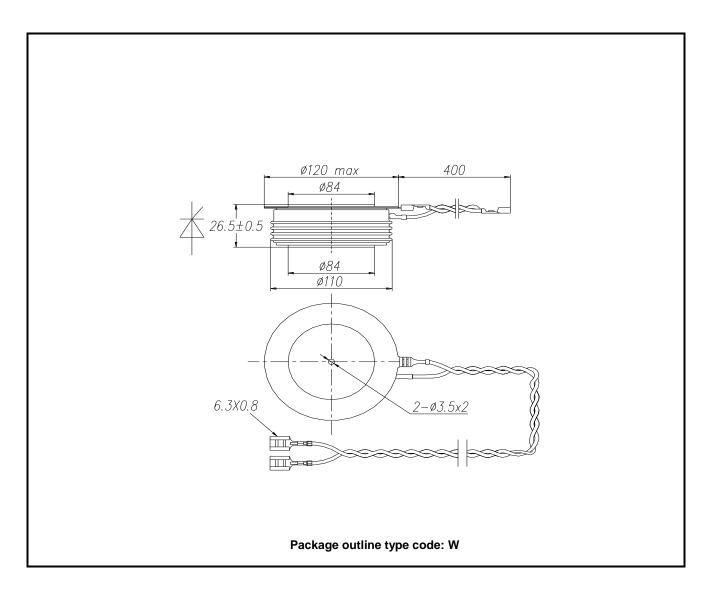


Fig.14 Package outline



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